

#### ABSTRACT OF THE DISCLOSURE

A semiconductor device is fabricated to have improved bitline contact formation. Polysilicon is deposited between gate contacts that connect to transistors of DRAM memory cells. The polysilicon covers the gate contacts and continues to cover the gate contacts during subsequent processing steps. A bitline of, e.g., tungsten, is deposited so that it contacts at least a portion of the polysilicon, thereby providing electrical contact with the DRAM transistors.

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